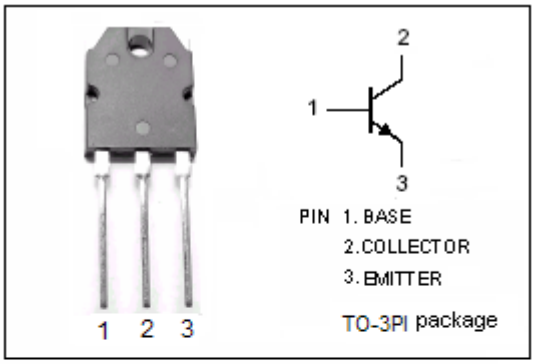
isc Silicon NPN Power Transistor 2SD1518

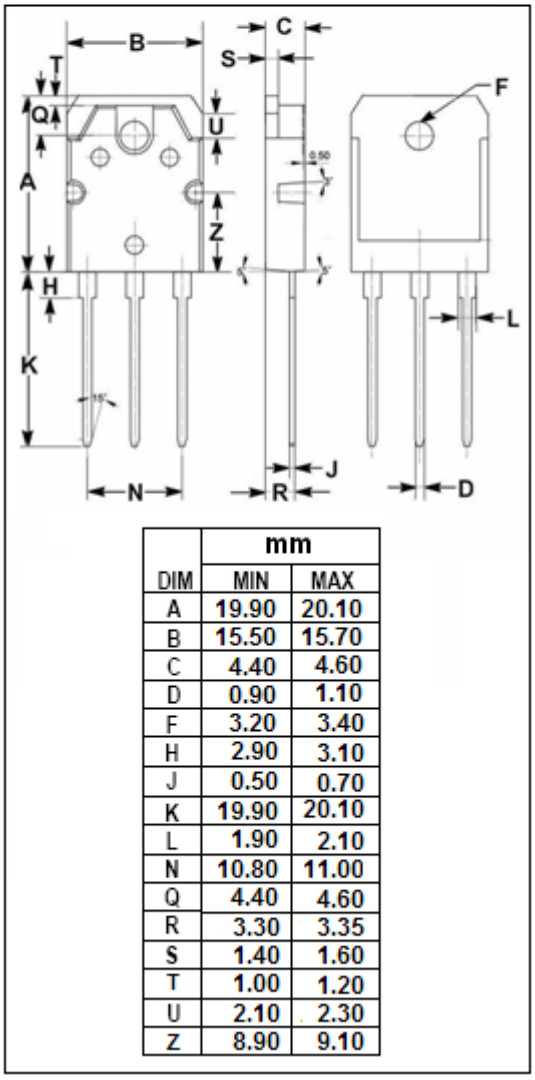


DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 400V(Min)
- High Switching Speed

APPLICATIONS

- Switching regulator and high voltage switching applications.



DIM	mm MIN	MAX
A	19.90	20.10
B	15.50	15.70
C	4.40	4.60
D	0.90	1.10
F	3.20	3.40
H	2.90	3.10
J	0.50	0.70
K	19.90	20.10
L	1.90	2.10
N	10.80	11.00
Q	4.40	4.60
R	3.30	3.35
S	1.40	1.60
T	1.00	1.20
U	2.10	2.30
Z	8.90	9.10

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	900	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base voltage	7	V
I_C	Collector Current-Continuous	6	A
I_{CM}	Collector Current-Pulse	10	A
I_B	Base Current-Continuous	3	A
P_C	Collector Power Dissipation @ T_C=25℃	50	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 2.5A; I_B= 0.5A			5.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 2.5A; I_B= 0.5A			1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= 900V; I_E= 0			1.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 7V; I_C= 0			1.0	mA
h_{FE-1}	DC Current Gain	I_C= 10mA ; V_{CE}= 5V	8			
h_{FE-2}	DC Current Gain	I_C= 0.6A; V_{CE}= 5V	10		40	
f_T	Current-Gain—Bandwidth Product	I_C= 0.1A; V_{CE}= 10V		5		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= 10V; f_{test}= 1.0MHz		75		pF
t_f	Fall Time	I_C= 2.5A; I_{B1}= 0.5A; I_{B2}= -1A			0.5	μs